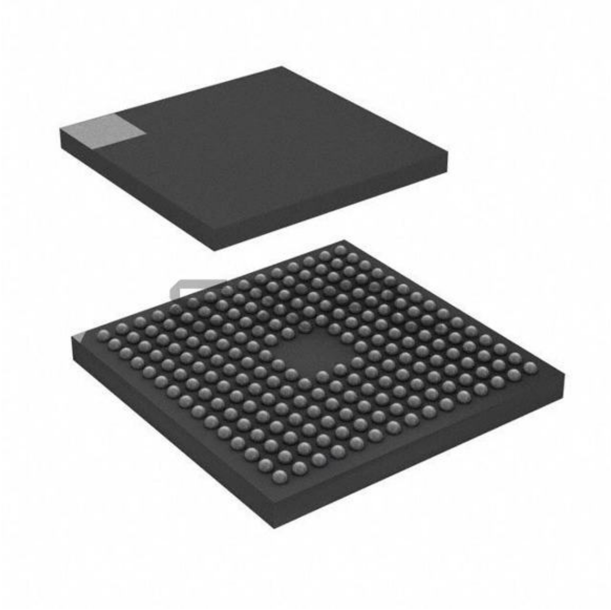
STMicroelectronics - STM32F777NIH6 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	159
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	216-TFBGA
Supplier Device Package	216-TFBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f777nih6

option bytes. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR}, without the need for an external reset circuit.

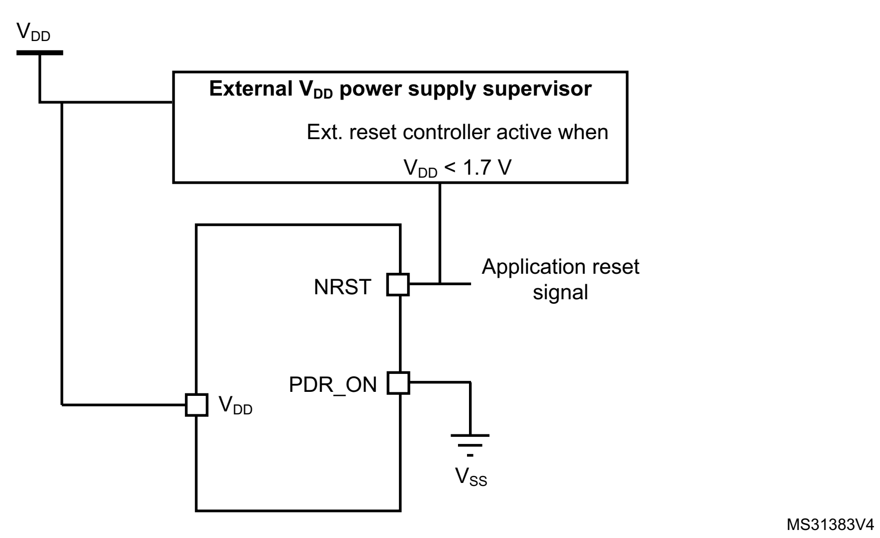
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

2.18.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled through the PDR_ON pin.

An external power supply supervisor should monitor V_{DD} and NRST and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to V_{SS}. Refer to *Figure 6: Power supply supervisor interconnection with internal reset OFF*.

Figure 6. Power supply supervisor interconnection with internal reset OFF



The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.7 V (see *Figure 7*).

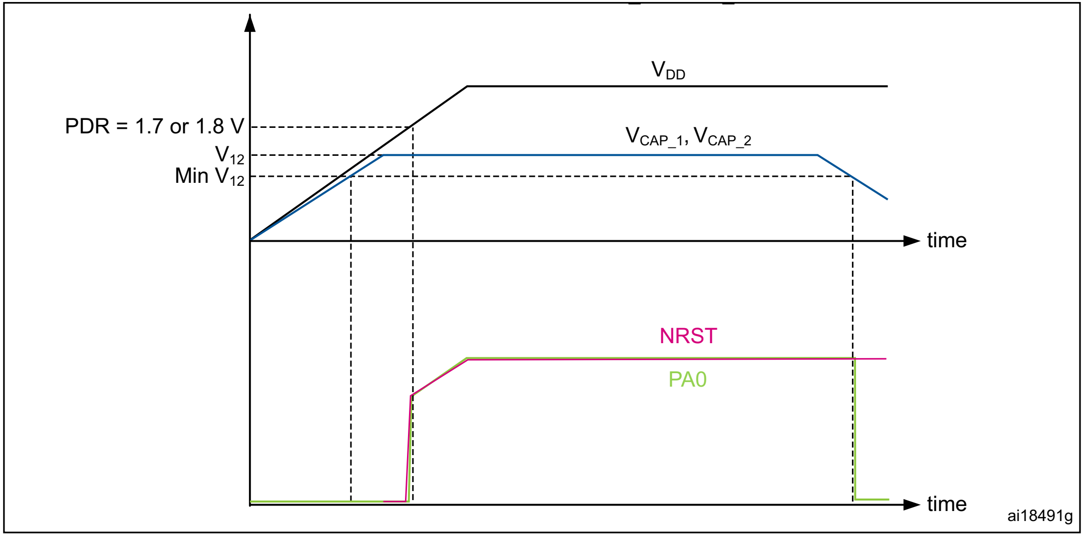
A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

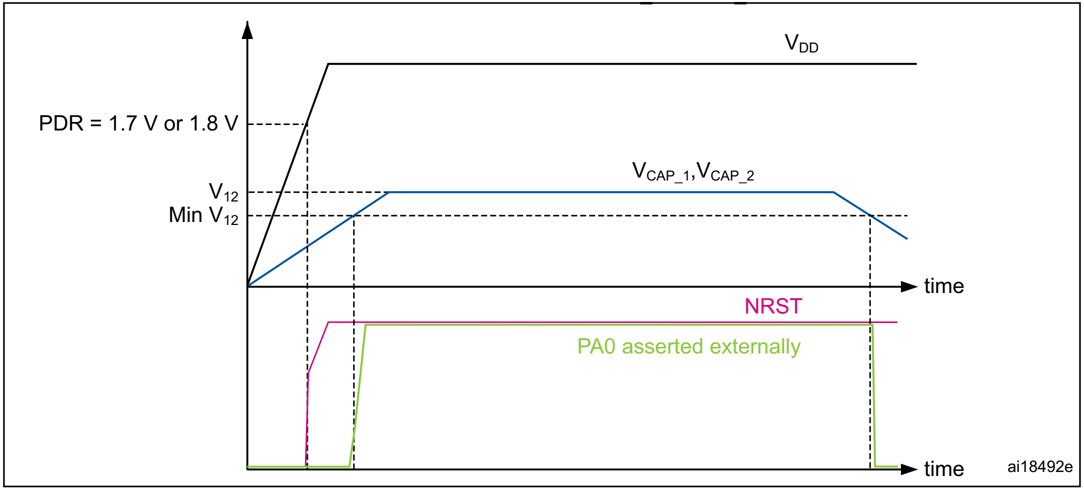
All the packages, except for the LQFP100, allow to disable the internal reset through the PDR_ON signal when connected to V_{SS}.

Figure 9. Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1},V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 10. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1},V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Table 10. STM32F777xx, STM32F778Ax and STM32F779xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F777xx						STM32F778Ax STM32F779xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180[(1)]	LQFP176	LQFP208	TFBGA216						
-	89	K14	108	131	N12	G1	112	131	N12	PG4	I/O	FT	-	FMC_A14/FMC_BA0, EVENTOUT	-
-	90	K13	109	132	N11	G2	113	132	N11	PG5	I/O	FT	-	FMC_A15/FMC_BA1, EVENTOUT	-
-	91	J15	110	133	J15	G3	114	133	J15	PG6	I/O	FT	-	FMC_NE3, DCMI_D12, LCD_R7, EVENTOUT	-
-	92	J14	111	134	J14	G4	115	134	J14	PG7	I/O	FT	-	SAI1_MCLK_A, USART6_CK, FMC_INT, DCMI_D13, LCD_CLK, EVENTOUT	-
-	93	H14	112	135	H14	G5	116	135	H14	PG8	I/O	FT	-	SPI6_NSS, SPDIF_RX2, USART6_RTS, ETH_PPS_OUT, FMC_SDCLK, LCD_G7, EVENTOUT	-
-	94	G12	113	136	G10	F1	117	136	G10	VSS	S		-	-	-
-	95	H13	114	137	G11	F2	118	137	G11	VDDUSB	S		-	-	-
63	96	H15	115	138	H15	G6	119	138	H15	PC6	I/O	FT	-	TIM3_CH1, TIM8_CH1, I2S2_MCK, DFSDM1_CKIN3, USART6_TX, FMC_NWAIT, SDMMC2_D6, SDMMC1_D6, DCMI_D0, LCD_HSYNC, EVENTOUT	-
64	97	G15	116	139	G15	F3	120	139	G15	PC7	I/O	FT	-	TIM3_CH2, TIM8_CH2, I2S3_MCK, DFSDM1_DATIN3, USART6_RX, FMC_NE1, SDMMC2_D7, SDMMC1_D7, DCMI_D1, LCD_G6, EVENTOUT	-

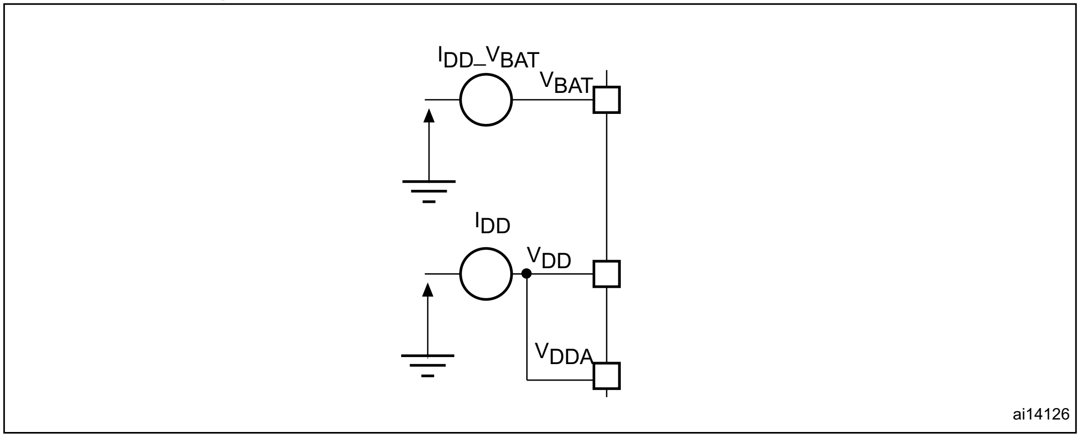
Table 12. STM32F777xx, STM32F778Ax and STM32F779xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	I2C4/UART5/TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/DFSDM1/CEC	I2C1/2/3/4/USART1/CEC	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5/6	SPI2/I2S2/SPI3/I2S3/SAI1/I2C4/UART4/DFSDM1	SPI2/I2S2/SPI3/I2S3/SPI6/USART1/2/3/UART5/DFSDM1/SPDIF	SPI6/SAI2/USART6/UART4/5/7/8/OTG_FS/SPDIF	CAN1/2/TIM12/13/14/QUADSPI/FMC/LCD	SAI2/QUADSPI/SDMMC2/DFSDM1/OTG2_HS/OTG1_FS/LCD	I2C4/CAN3/SDMMC2/ETH	UART7/FMC/SDMMC1/MDIOS/OTG2_FS	DCMI/LCD/DSI	LCD	SYS
Port F	PF12	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	I2C4_SMBA	-	DFSDM1_DATAIN6	-	-	-	-	-	FMC_A7	-	-	EVENTOUT
	PF14	-	-	-	-	I2C4_SCL	-	DFSDM1_CKIN6	-	-	-	-	-	FMC_A8	-	-	EVENTOUT
	PF15	-	-	-	-	I2C4_SDA	-	-	-	-	-	-	-	FMC_A9	-	-	EVENTOUT
Port G	PG0	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A10	-	-	EVENTOUT
	PG1	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A11	-	-	EVENTOUT
	PG2	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A12	-	-	EVENTOUT
	PG3	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A13	-	-	EVENTOUT
	PG4	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A14/FMC_BA0	-	-	EVENTOUT
	PG5	-	-	-	-	-	-	-	-	-	-	-	-	FMC_A15/FMC_BA1	-	-	EVENTOUT
	PG6	-	-	-	-	-	-	-	-	-	-	-	-	FMC_NE3	DCMI_D12	LCD_R7	EVENTOUT
	PG7	-	-	-	-	-	-	SAI1_MCLK_A	-	USART6_CK	-	-	-	FMC_INT	DCMI_D13	LCD_CLK	EVENTOUT

Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} ...) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure good operation of the device. It is not recommended to remove filtering capacitors to reduce PCB size or cost. This might cause incorrect operation of the device.

5.1.7 Current consumption measurement

Figure 26. Current consumption measurement scheme



5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 14: Voltage characteristics*, *Table 15: Current characteristics*, and *Table 16: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and the functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. The device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Table 14. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage (including V_{DDA}, V_{DD}, V_{BAT}, V_{DDUSB}, V_{DDDSI} (1) and $V_{DDSDMMC}$)(2)	− 0.3	4.0	V
V_{IN}	Input voltage on FT pins(3)	V_{SS} − 0.3	V_{DD}+4.0	
	Input voltage on TTa pins	V_{SS} − 0.3	4.0	
	Input voltage on any other pin	V_{SS} − 0.3	4.0	
	Input voltage on BOOT pin	V_{SS}	9.0	
$\|\Delta V_{DDx}\|$	Variations between different V_{DD} power pins	-	50	mV
$\|V_{SSX} - V_{SS}\|$	Variations between all the different ground pins(4)	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 5.3.18: Absolute maximum ratings (electrical sensitivity)*		-

1. Applicable only for STM32F7x9 sales types.
2. All main power (V_{DD}, V_{DDA}, $V_{DDSDMMC}$, V_{DDUSB}, V_{DDDSI}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
3. V_{IN} maximum value must always be respected. Refer to *Table 15* for the values of the maximum allowed injected current.
4. Include V_{REF-} pin.

Table 15. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD_x} power lines (source)(1)	420	mA
ΣI_{VSS}	Total current out of sum of all V_{SS_x} ground lines (sink)(1)	−420	
ΣI_{VDDUSB}	Total current into V_{DDUSB} power line (source)	25	
$\Sigma I_{VDDSDMMC}$	Total current into $V_{DDSDMMC}$ power line (source)	60	
I_{VDD}	Maximum current into each V_{DD_x} power line (source)(1)	100	
$I_{VDDSDMMC}$	Maximum current into $V_{DDSDMMC}$ power line (source): PG[12:9], PD[7:6]	100	
I_{VSS}	Maximum current out of each V_{SS_x} ground line (sink)(1)	−100	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current sourced by any I/Os and control pin	−25	
ΣI_{IO}	Total output current sunk by sum of all I/O and control pins (2)	120	
	Total output current sunk by sum of all USB I/Os	25	
	Total output current sunk by sum of all SDMMC I/Os	120	
	Total output current sourced by sum of all I/Os and control pins except USB I/Os(2)	−120	
$I_{INJ(PIN)}$	Injected current on FT, FTf, RST and B pins (3)	−5/+0	
	Injected current on TTa pins(4)	±5	
$\Sigma I_{INJ(PIN)}$(4)	Total injected current (sum of all I/O and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN}>V_{DDA}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 14: Voltage characteristics* for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 16. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	– 65 to +150	°C
T_J	Maximum junction temperature	125	

Low-speed internal (LSI) RC oscillator

Table 46. LSI oscillator characteristics [1]

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}[2]	Frequency	17	32	47	kHz
$t_{su(LSI)}$[3]	LSI oscillator startup time	-	15	40	µs
$I_{DD(LSI)}$[3]	LSI oscillator power consumption	-	0.4	0.6	µA

1. V_{DD} = 3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

Figure 33. LSI deviation versus temperature

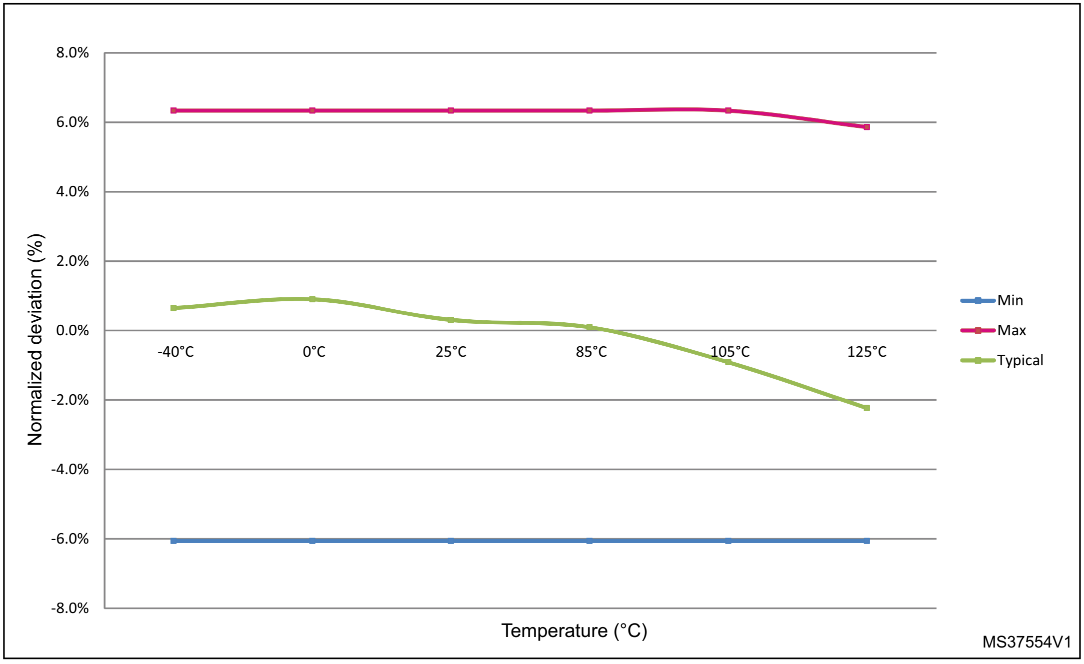


Table 49. PLLISAI characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{LOCK}	PLLSAI lock time	VCO freq = 192 MHz		75	-	200	µs
		VCO freq = 432 MHz		100	-	300	
Jitter[3]	Master SAI clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-	
			peak to peak	-	±280	-	ps
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples		-	90	-	ps
	FS clock jitter	Cycle to cycle at 48 KHz on 1000 samples		-	400	-	ps
$I_{DD(PLLSAI)}$[4]	PLLSAI power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLSAI)}$[4]	PLLSAI power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

5.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 61: EMI characteristics*). It is available only on the main PLL.

Table 50. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max[1]	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15} - 1$	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$\text{MODEPER} = \text{round}[f_{PLL\_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

Table 51. MIPI D-PHY characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Output low level voltage	-	1.1	1.2	1.2	V
$V_{IL-ULPS}$	Output high level voltage	-	-50	-	50	mV
V_{IH}	Output impedance of LP transmitter	-	110	-	-	Ω
V_{hys}	15%-85% rise and fall time	-	-	-	25	ns
LP Contention Detector Characteristics						
V_{ILCD}	Logic 0 contention threshold	-	-	-	200	mV
V_{IHCD}	Logic 0 contention threshold	-	450	-	-	

1. Guaranteed based on test during characterization.

Table 52. MIPI D-PHY AC characteristics LP mode and HS/LP transitions(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{LPX}	Transmitted length of any Low-Power state period	-	50	-	-	ns
$T_{CLK-PREPARE}$	Time that the transmitter drives the Clock Lane LP-00 Line state immediately before the HS-0 Line state starting the HS transmission.	-	38	-	95	
$T_{CLK-PREPARE}$ + $T_{CLK-ZERO}$	Time that the transmitter drives the HS-0 state prior to starting the clock.	-	300	-	-	
$T_{CLK-PRE}$	Time that the HS clock shall be driven by the transmitter prior to any associated Data Lane beginning the transition from LP to HS mode.	-	8	-	-	UI

Table 56. Flash memory programming (single bank configuration nDBANK=1) (continued)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{prog}	Programming voltage	32-bit program operation	2.7	-	3	V
		16-bit program operation	2.1	-	3.6	V
		8-bit program operation	1.7	-	3.6	V

1. Guaranteed by characterization results.
2. The maximum programming time is measured after 100K erase operations.

Table 57. Flash memory programming (dual bank configuration nDBANK=0)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	250	600	
		Program/erase parallelism (PSIZE) = x 32	-	200	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1100	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	800	1400	
		Program/erase parallelism (PSIZE) = x 32	-	500	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2.1	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.5	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	

I^2S interface characteristics

Unless otherwise specified, the parameters given in *Table 86* for the I^2S interface are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 86. I^2S dynamic characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256x8K	256xFs(2)	MHz
f_{CK}	I2S clock frequency	Master data	-	64xFs	MHz
		Slave data	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	-	3	ns
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	5	-	
$t_{h(WS)}$	WS hold time	Slave mode	2	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	2.5	-	
$t_{su(SD\_SR)}$		Slave receiver	2.5	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	3.5	-	
$t_{h(SD\_SR)}$		Slave receiver	2	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	12	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	3	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	0	-	

1. Guaranteed by characterization results.
2. The maximum value of 256xFs is 49.152 MHz (APB1 maximum frequency).

*Note: Refer to RM0410 reference manual I2S section for more details about the sampling frequency (F_S). f_{MCK}, f_{CK}, and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). F_S maximum value is supported for each mode/condition.*

Figure 64. Asynchronous multiplexed PSRAM/NOR write waveforms

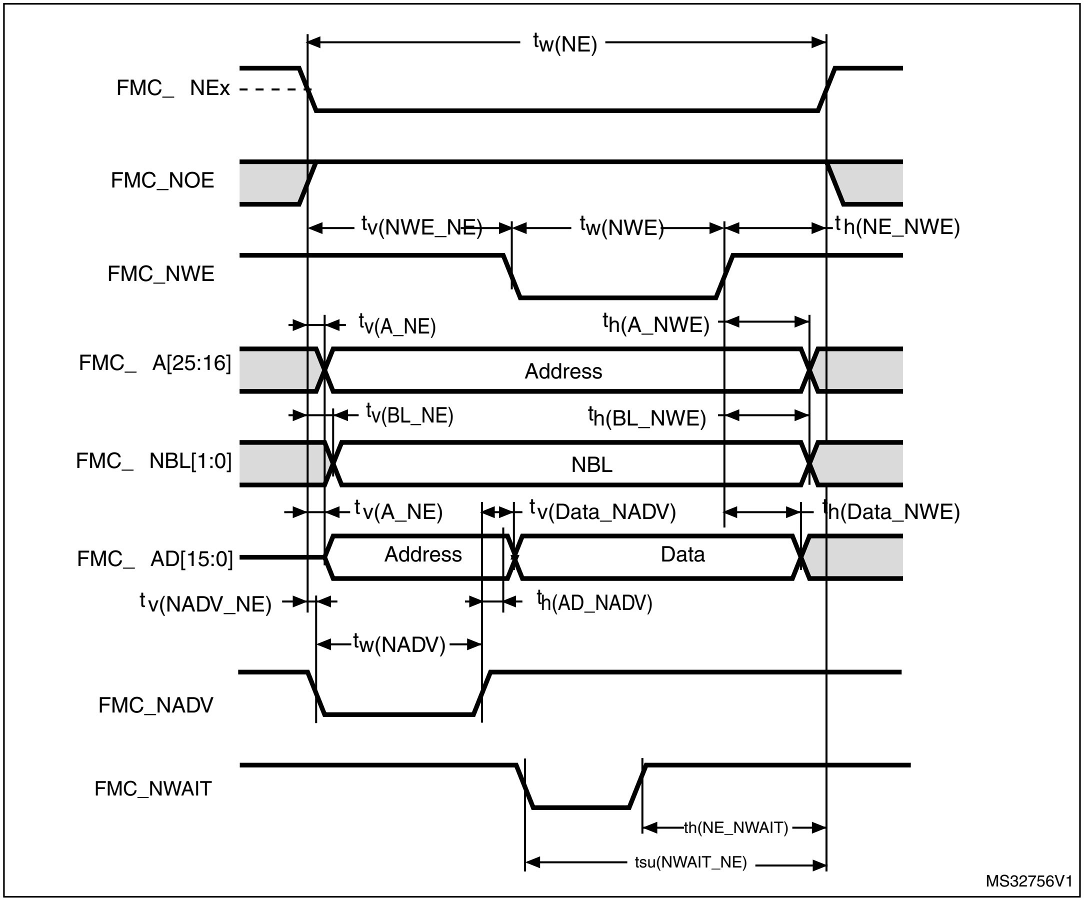


Table 106. Asynchronous multiplexed PSRAM/NOR write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK} - 1$	$4T_{HCLK} + 1$	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK} - 1$	$T_{HCLK} + 0.5$	
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	$T_{HCLK} - 0.5$	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	T_{HCLK}	$T_{HCLK} + 1$	
$t_{h(AD\_NADV)}$	FMC_AD(adress) valid hold time after FMC_NADV high)	$T_{HCLK} - 0.5$	-	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	$T_{HCLK} + 0.5$	-	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK} - 0.5$	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK} + 2$	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK} + 0.5$	-	

Table 109. Synchronous multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK} - 0.5$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	$T_{HCLK} + 0.5$	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	1	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	2 .5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK} + 0.5$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	3	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	3.5	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	-	2	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK} + 0.5$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

5.3.34 Digital filter for Sigma-Delta Modulators (DFSDM) characteristics

Unless otherwise specified, the parameters given in *Table 122* for DFSDM are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30pF
- Measurement points are done at CMOS levels: 0.5 x VDD

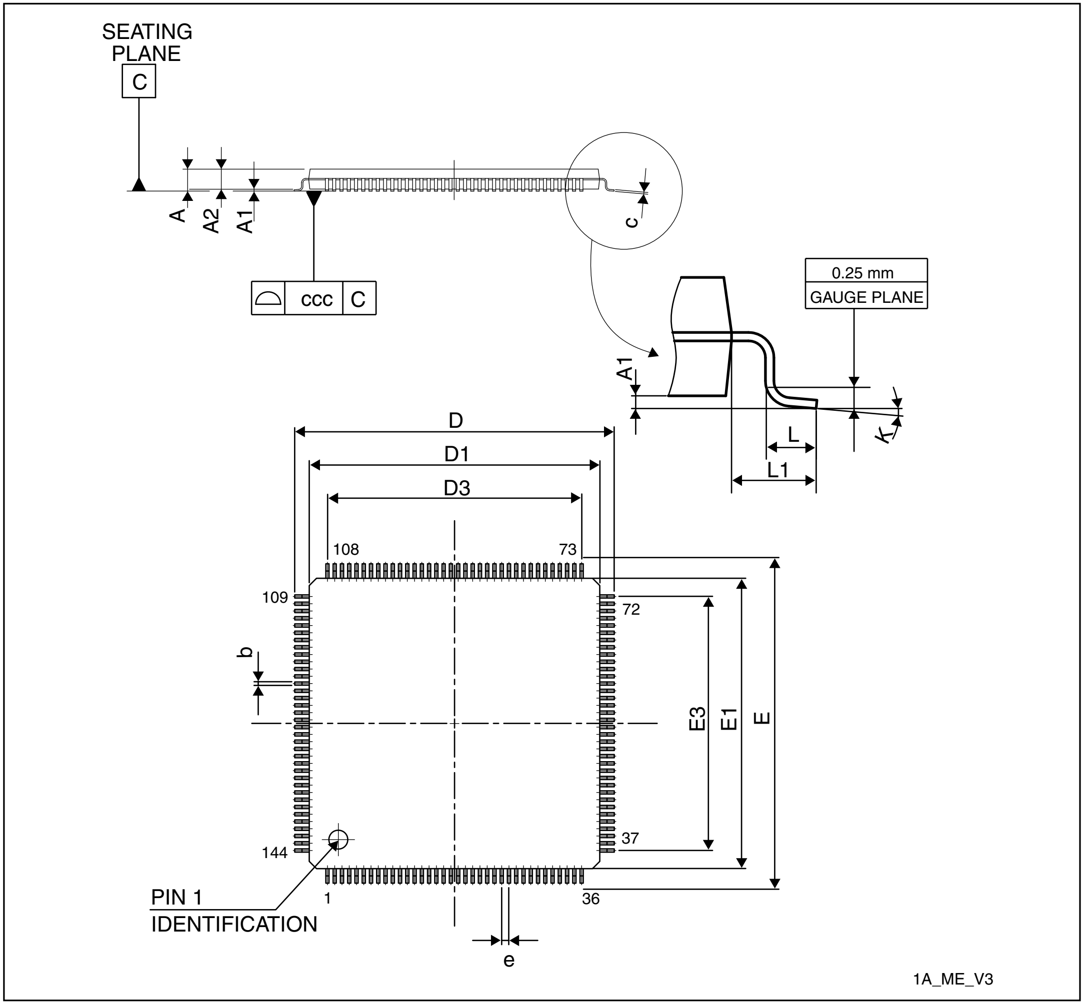
Refer to *Section 5.3.20: I/O port characteristics* for more details on the input/output alternate function characteristics (DFSDM1_CKINx, DFSDM1_DATINx, DFSDM1_CKOUT for DFSDM1).

Table 122. DFSDM measured timing 1.71-3.6V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	$1.71 < V_{DD} < 3.6$ V	-	-	f_{SYSCLK}	MHz
f_{CKIN} $(1/T_{CKIN})$	Input clock frequency	SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), $1.71 < V_{DD} < 3.6$ V	-	-	20 $(f_{DFSDMCLK}/4)$	
		SPI mode (SITP[1:0]=0,1), External clock mode (SPICKSEL[1:0]=0), $2.7 < V_{DD} < 3.6$ V	-	-	20 $(f_{DFSDMCLK}/4)$	
		SPI mode (SITP[1:0]=0,1), Internal clock mode (SPICKSEL[1:0]≠0), $1.71 < V_{DD} < 3.6$ V	-	-	20 $(f_{DFSDMCLK}/4)$	
		SPI mode (SITP[1:0]=0,1), Internal clock mode (SPICKSEL[1:0]≠0), $2.7 < V_{DD} < 3.6$ V	-	-	20 $(f_{DFSDMCLK}/4)$	
f_{CKOUT}	Output clock frequency	$1.71 < V_{DD} < 3.6$ V	-	-	20	
$DuCy_{CKOUT}$	Output clock frequency duty cycle	$1.71 < V_{DD} < 3.6$ V	45	50	55	%

6.2 LQFP144 20 x 20 mm, low-profile quad flat package information

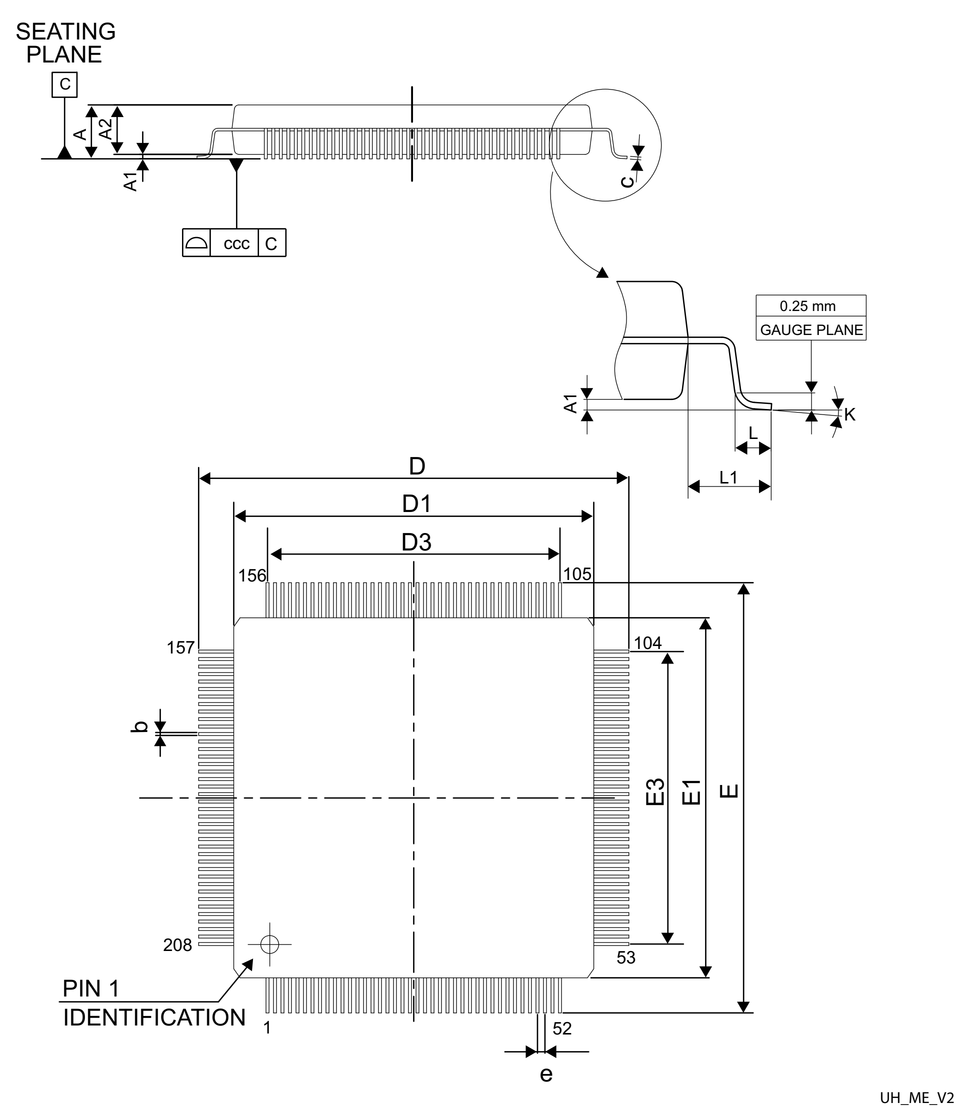
Figure 86. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package outline



1. Drawing is not to scale.

6.4 LQFP208 28 x 28 mm low-profile quad flat package information

Figure 92. LQFP208, 28 x 28 mm, 208-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 133. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
G	-	0.900	-	-	0.0354	-
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 102. TFBGA216, 13 x 13 mm, 0.8 mm pitch, thin fine-pitch ball grid array package recommended footprint

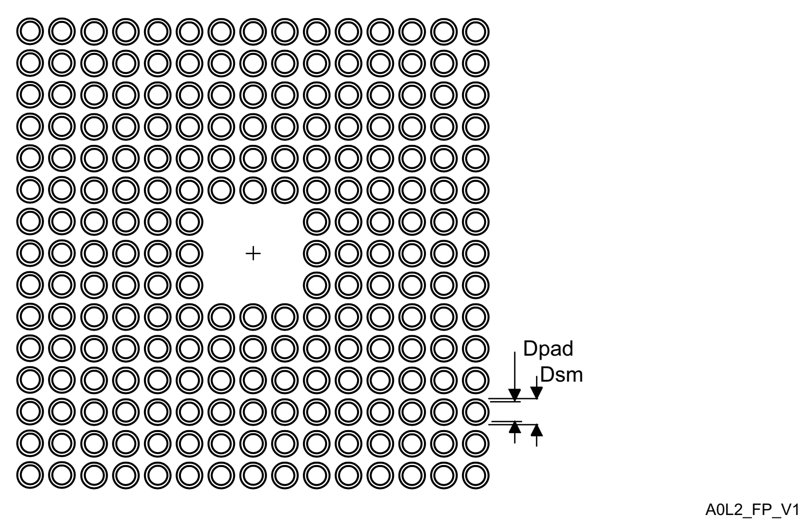


Table 134. TFBGA216 recommended PCB design rules (0.8 mm pitch BGA)

Dimension	Recommended values
Pitch	0.8
Dpad	0.400 mm
Dsm	0.470 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.400 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.120 mm

Appendix A Recommendations when using internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry must be disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD}
- The over-drive mode is not supported

A.1 Operating conditions

Table 137. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states [1][2]	I/O operation	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V[3]	Conversion time up to 1.2 Msps	20 MHz	168 MHz with 8 wait states and over-drive OFF	– No I/O compensation	8-bit erase and program operations only

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from the Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V, with the use of an external power supply supervisor (refer to *Section 2.18.1: Internal reset ON*).

Revision history

Table 138. Document revision history

Date	Revision	Changes
21-Mar-2016	1	Initial release.
26-Apr-2016	2	DFSDM replaced by DFSDM1 in: – *Table 10: STM32F777xx, STM32F778Ax and STM32F779xx pin and ball definitions*. – *Table 12: STM32F777xx, STM32F778Ax and STM32F779xx alternate function mapping* . – *Table 13: STM32F777xx, STM32F778Ax and STM32F779xx register boundary addresses*. – *Section 5.3.34: Digital filter for Sigma-Delta Modulators (DFSDM) characteristics*. Updated *Table 2: STM32F777xx, STM32F778Ax and STM32F779xx features and peripheral counts* adding DFSDM1 features. Updated *Table 39: Peripheral current consumption* adding DFSDM1 current consumption. Updated cover in 2 pages. Updated cover replacing for SPI ‘up to 50 Mbit/s’ by ‘up to 54 Mbit/s’.
06-May-2016	3	Updated *Table 2: STM32F777xx, STM32F778Ax and STM32F779xx features and peripheral counts* GPIO number. Updated *Table 12: STM32F777xx, STM32F778Ax and STM32F779xx alternate function mapping* adding CAN3_RX alternate function on PA8/AF11.
22-Dec-2016	4	Updated *Table 97: Dynamics characteristics: Ethernet MAC signals for RMII*. Updated *Table 71: ADC characteristics* sampling rate. Updated all the notes removing ‘not tested in production’. Updated *Figure 46: SPI timing diagram - slave mode and CPHA = 0* and *Figure 47: SPI timing diagram - slave mode and CPHA = 1(1)* with modified NSS timing waveforms (among other changes). Updated *Table 121: LTDC characteristics* clock output frequency at 65 MHz. Updated *Section 5.2: Absolute maximum ratings*. Updated *Section 6: Package information* adding information about other optional marking or inset/upset marks.